

Fig. 3  
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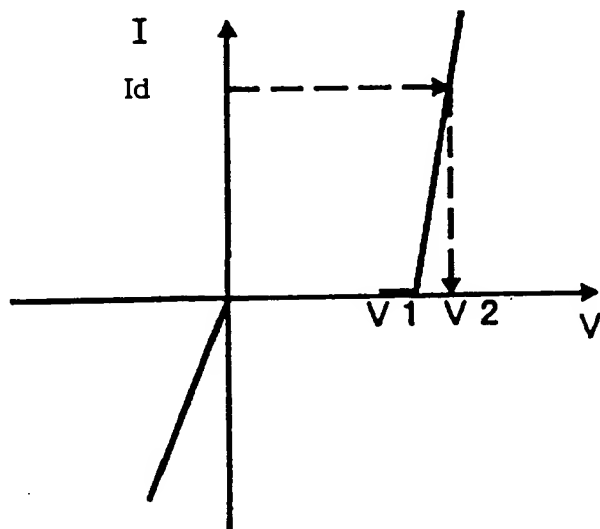


Fig. 4  
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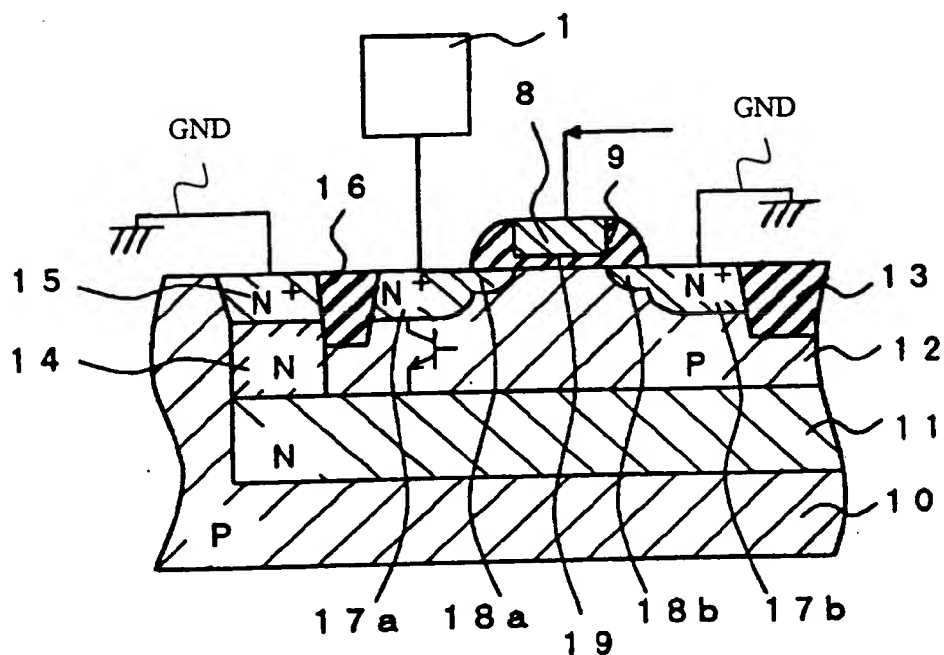


Fig. 5

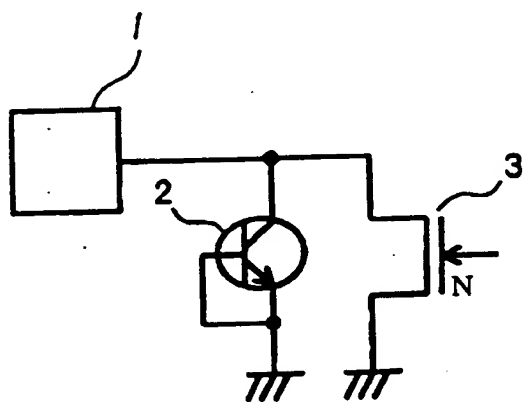


Fig. 6

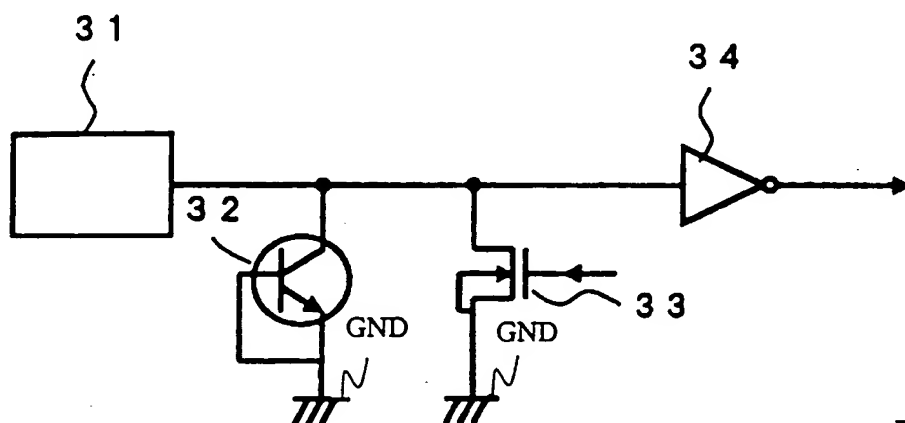


Fig. 15

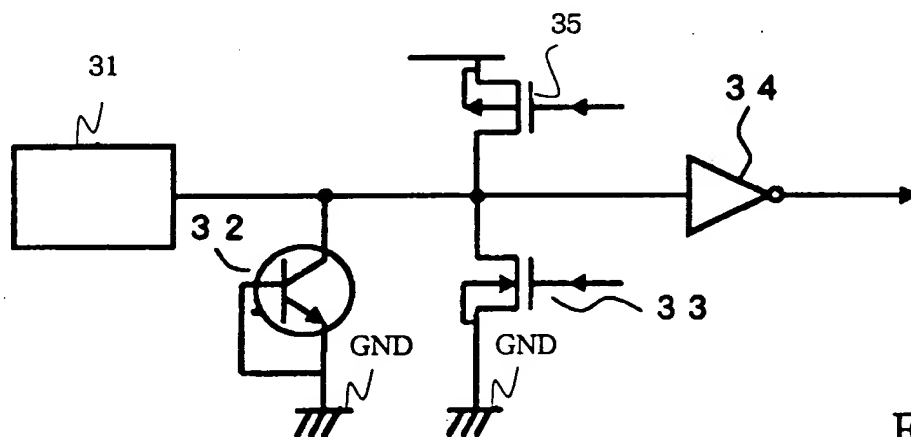


Fig. 16

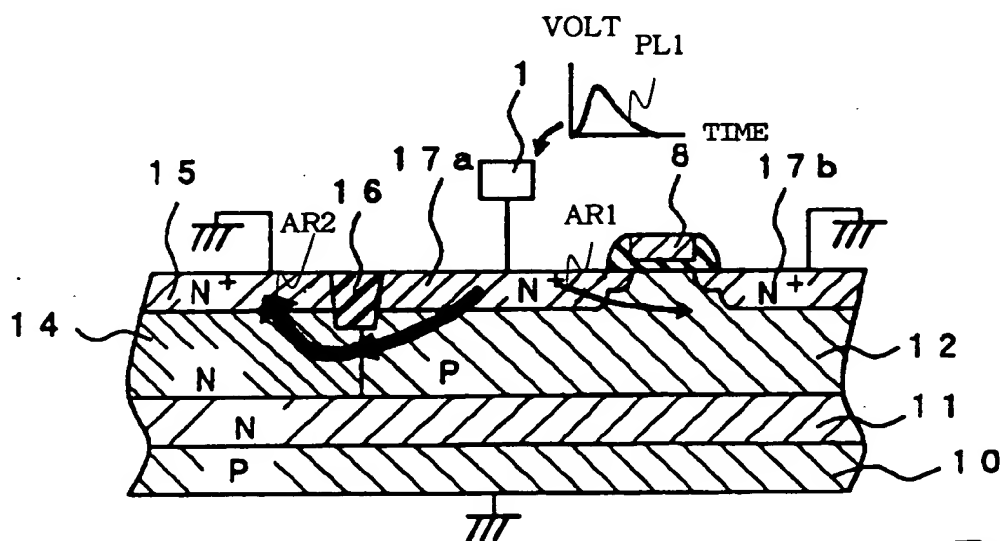


Fig. 7



The diagram illustrates a cross-section of a semiconductor device, specifically a 'Deep nwell' structure. The vertical axis represents 'Distance (Microns)' from 0.00 to 3.00, and the horizontal axis represents 'Distance (Microns)' from 0.00 to 5.00. The structure shows a deep n-well (indicated by diagonal hatching) and other doped regions (indicated by different hatching patterns like horizontal lines, vertical lines, and cross-hatching). A dashed line indicates the surface of the device.

Fig. 6

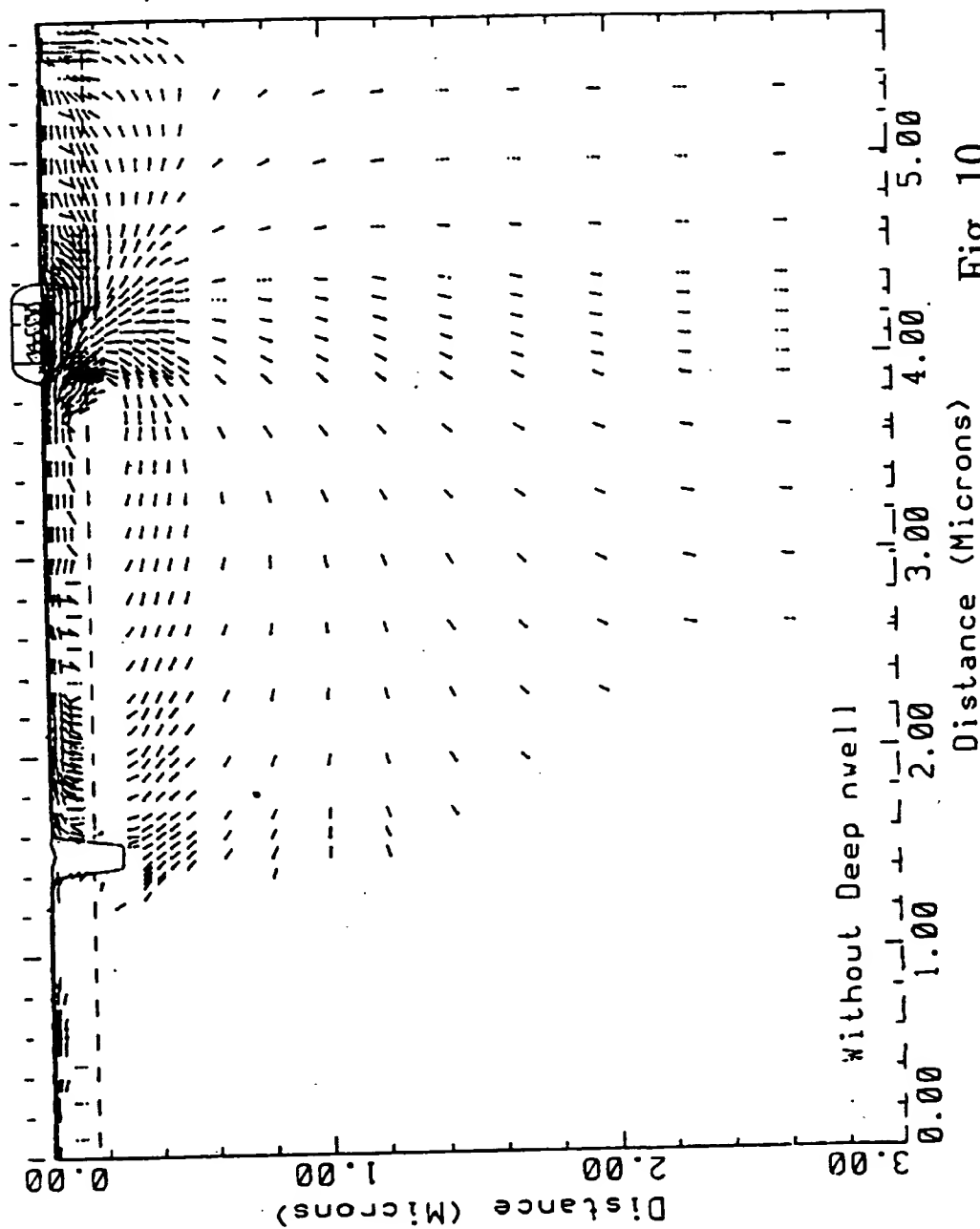
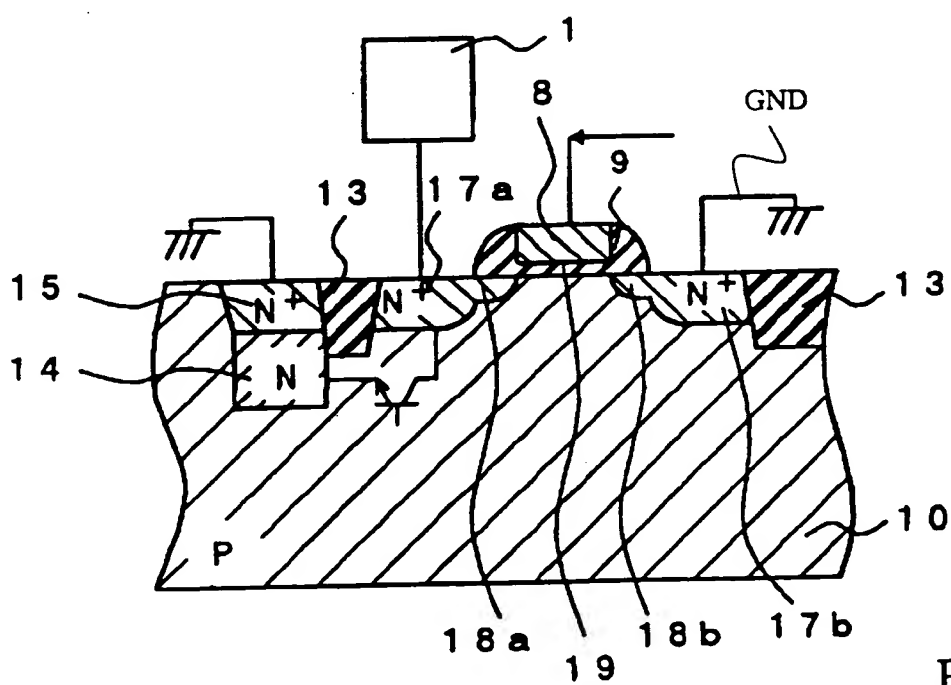
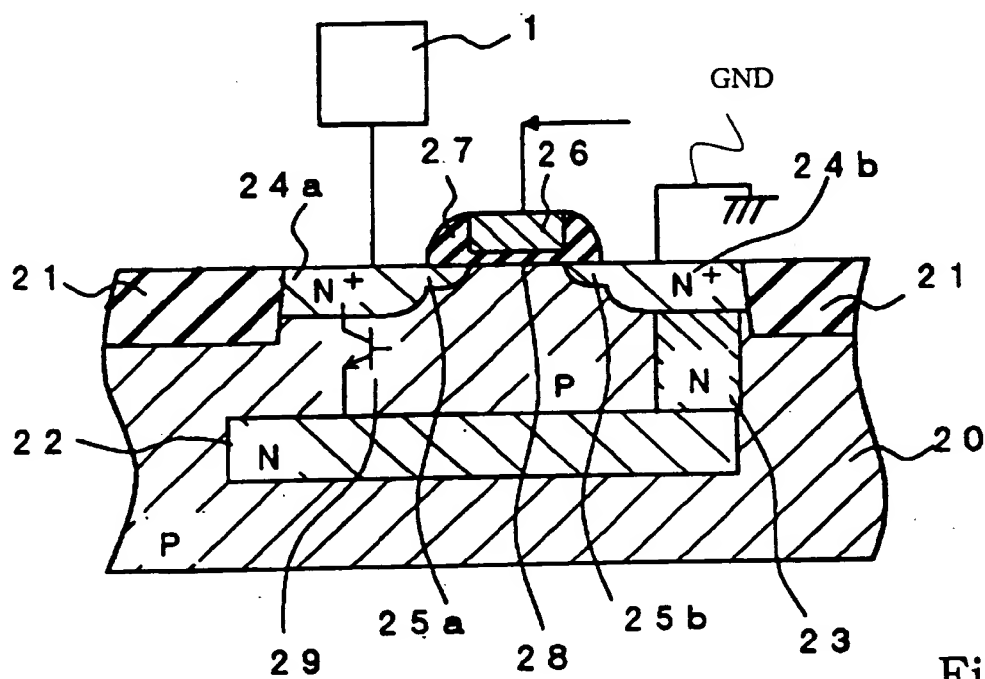
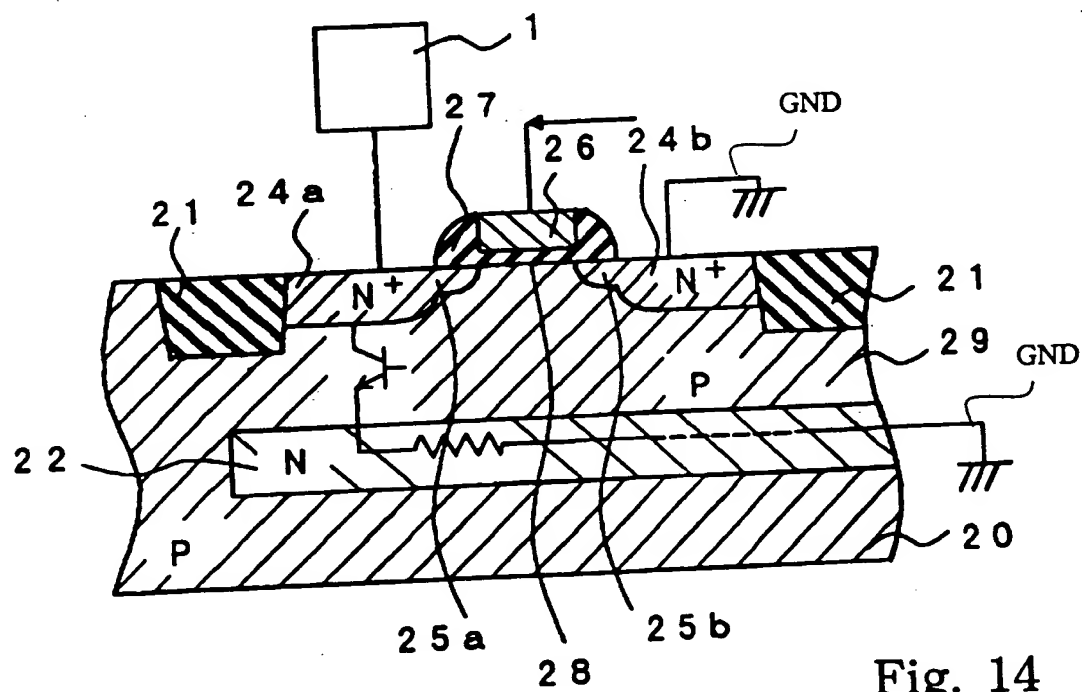
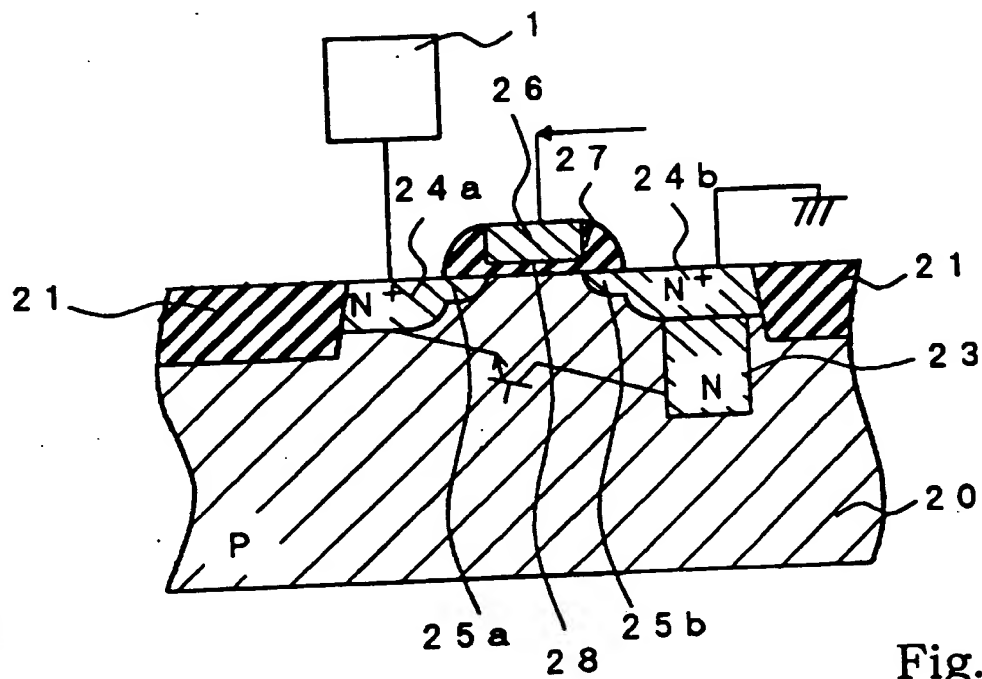


Fig. 10  
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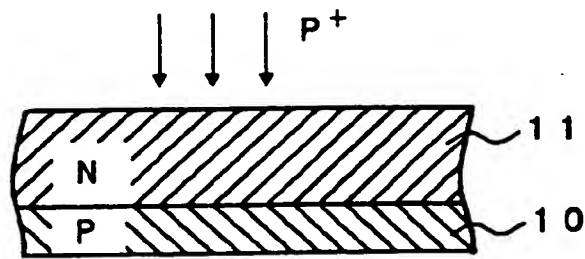


Fig. 17A

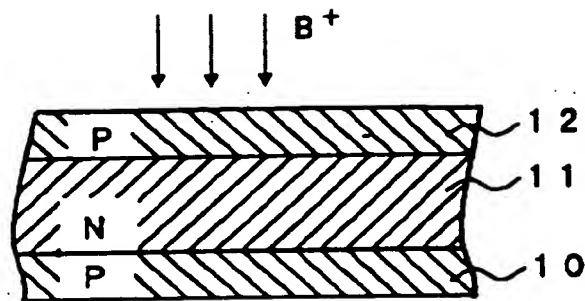


Fig. 17B

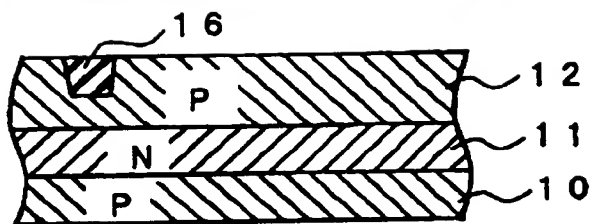


Fig. 17C

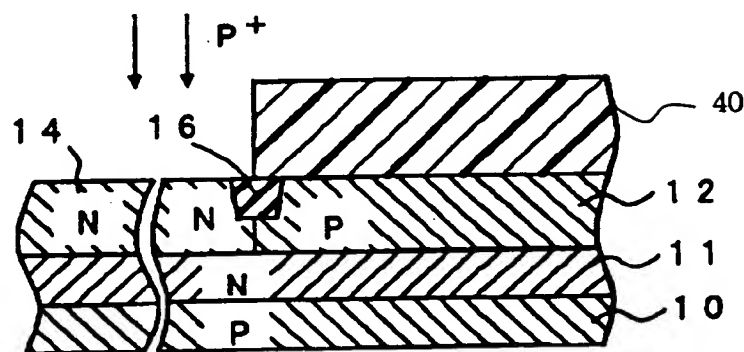


Fig. 17D

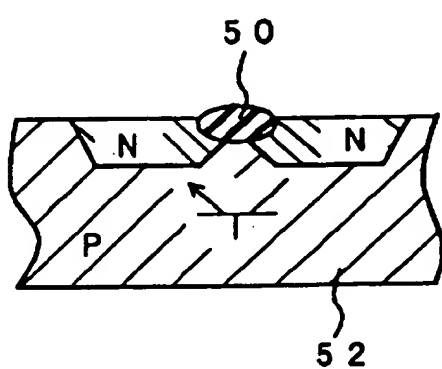
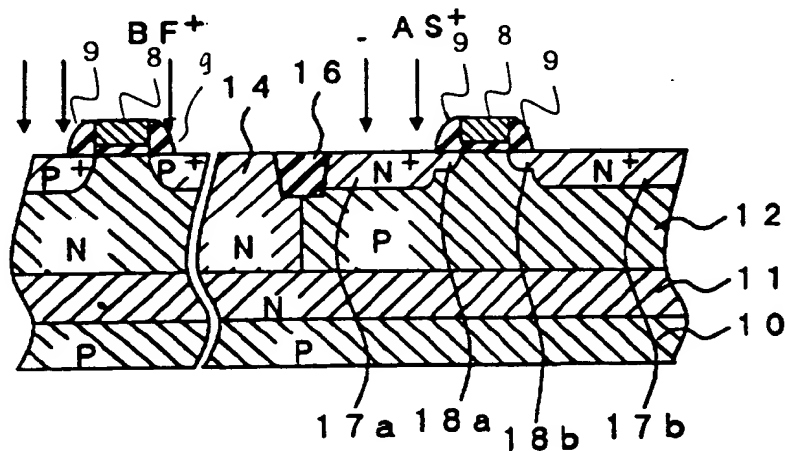
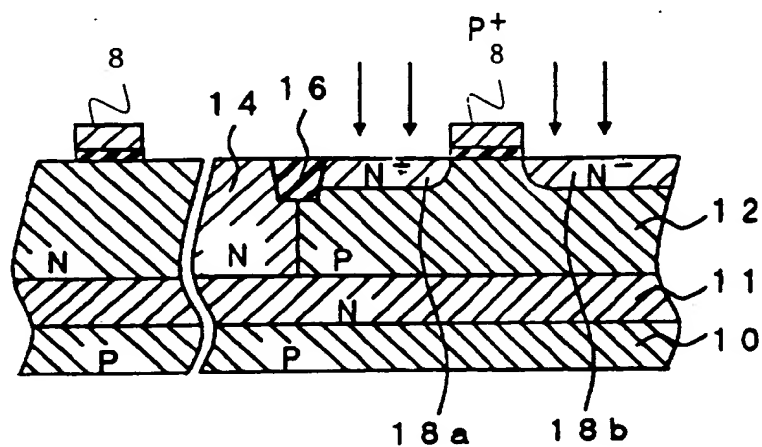


Fig. 1A  
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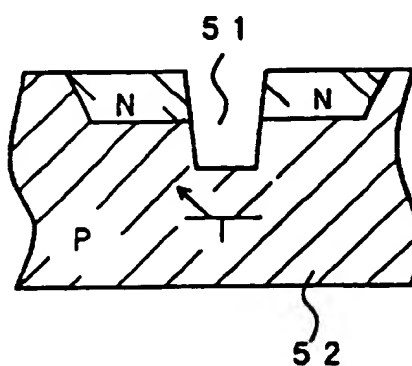


Fig. 1B  
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